TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

HN1A01FE

Audio Frequency General Purpose Amplifier Applications

- Small package (Dual type)
- High voltage and high current

: $V_{CEO} = -50V$, $I_{C} = -150mA$ (max)

High h_{FE} : $h_{FE} = 120~400$

Excellent hFE linearity

: $h_{FE} (I_C = -0.1 \text{mA}) / h_{FE} (I_C = -2 \text{mA}) = 0.95 \text{ (typ.)}$

Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	-50	V	
Collector-emitter voltage	V _{CEO}	-50	V	
Emitter-base voltage	V _{EBO}	-5	V	
Collector current	Ic	-150	mA	
Base current	I _B	-30	mA	
Collector power dissipation	P _C *	100	mW	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55~150	°C	

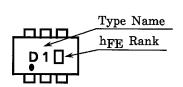
Electrical Characteristics (Ta = 25°C) (Q1,Q2 Common)

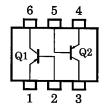
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	$V_{CB} = -50V$, $I_E = 0$	_	_	-0.1	μA
Emitter cut-off current	I _{EBO}	_	$V_{EB} = -5V, I_{C} = 0$	_	_	-0.1	μΑ
DC current gain	h _{FE (Note)}	_	$V_{CE} = -6V, I_{C} = -2mA$	120	_	400	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = -100mA, I _B = -10mA	_	-0.1	-0.3	V
Transition frequency	f _T	_	$V_{CE} = -10V, I_{C} = -1mA$	80	_	_	MHz
Collector output capacitance	C _{ob}	_	$V_{CB} = -10V$, $I_E = 0$, $f = 1MHz$	_	4	_	pF

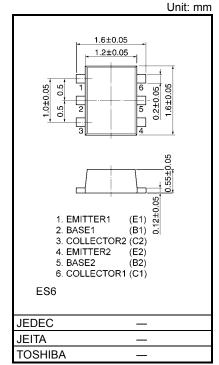
h_{FE} Classification Y (Y): 120~240, GR (G): 200~400 () Marking Symbol Note:

Marking

Equivalent Circuit (Top View)



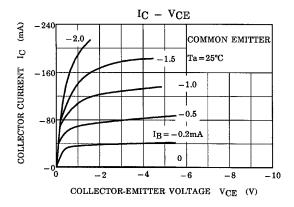


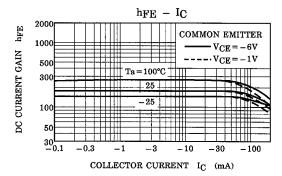


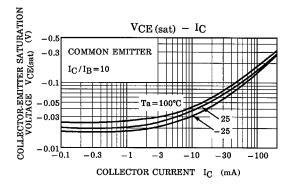
Weight: 3.0mg(typ.)

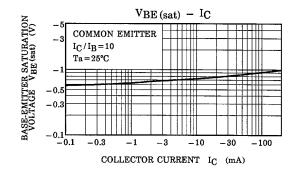
^{*}Total rating

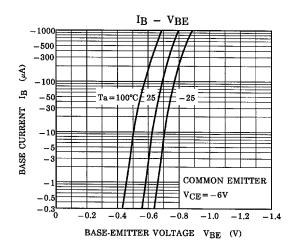
(Q1,Q2 Common)

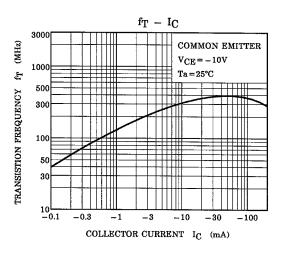


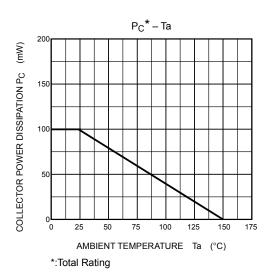












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Handbook" etc..

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